2SD1366A

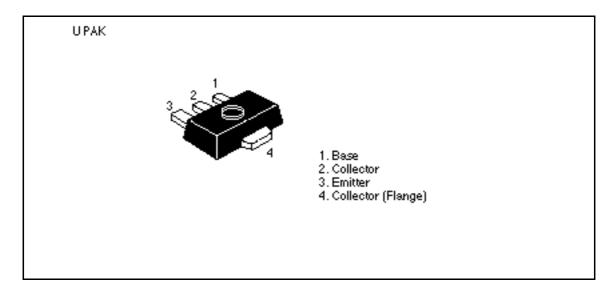
Silicon NPN Epitaxial

HITACHI

Application

Low frequency power amplifier

Outline





2SD1366A

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	30	V
Collector to emitter voltage	V_{CEO}	25	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I _c	1	А
Collector peak current	i _{C(peak)} *1	1.5	А
Collector power dissipation	P _C *2	1	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW 10 ms, Duty cycle 20%.

2. Value on the alumina ceramic board (12.5 \times 20 \times 0.7 mm)

Electrical Characteristics ($Ta = 25^{\circ}C$)

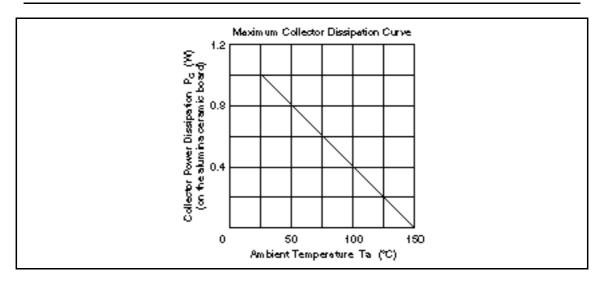
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	_	_	V	$I_{c} = 10 \ \mu A, \ I_{e} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	25	_	_	V	$I_C = 1 \text{ mA}, R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	V	$I_{E} = 10 \ \mu A, \ I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	0.1	μΑ	$V_{CB} = 20 \text{ V}, I_{E} = 0$
Emitter cutoff current	I _{EBO}	_		0.1	μΑ	$V_{EB} = 4 \text{ V}, I_{C} = 0$
DC current transfer ratio	h _{FE} *1	85	_	240		V_{CE} = 2 V, I_C = 0.5 A, Pulse
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	0.15	0.3	V	$I_{\rm C} = 0.8 \text{ A}, I_{\rm B} = 0.08 \text{ A}, \text{ Pulse}$
Base to emitter saturation voltage	$V_{BE(sat)}$	_	0.9	1.0	V	$I_{\rm C} = 0.8 \text{ A}, I_{\rm B} = 0.08 \text{ A}, \text{ Pulse}$
Gain bandwidth product	f _T	_	240	_	MHz	V_{CE} = 2 V, I_C = 0.5 A, Pulse
Collector output capacitance	Cob	_	22	_	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$

Note: 1. The 2SD1366A is grouped by h_{FE} as follows.

Mark	AC	AD
h _{FE}	85 to 170	120 to 240

See characteristic curves of 2SD1366.

2SD1366A



When using this document, keep the following in mind:

- 1. This document may, wholly or partially, be subject to change without notice.
- 2. All rights are reserved: No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without Hitachi's permission.
- 3. Hitachi will not be held responsible for any damage to the user that may result from accidents or any other reasons during operation of the user's unit according to this document.
- 4. Circuitry and other examples described herein are meant merely to indicate the characteristics and performance of Hitachi's semiconductor products. Hitachi assumes no responsibility for any intellectual property claims or other problems that may result from applications based on the examples described herein.
- 5. No license is granted by implication or otherwise under any patents or other rights of any third party or Hitachi, Ltd.
- 6. MEDICAL APPLICATIONS: Hitachi's products are not authorized for use in MEDICAL APPLICATIONS without the written consent of the appropriate officer of Hitachi's sales company. Such use includes, but is not limited to, use in life support systems. Buyers of Hitachi's products are requested to notify the relevant Hitachi sales offices when planning to use the products in MEDICAL APPLICATIONS.

HITACHI

Hitachi, Ltd.
Semiconductor & IC Div.
hippon Bidg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokiyo 100, Japan
Tet Tokiyo (03, 3270-2111
Fex: (03, 3270-5100

For further in formation write to:

Hitachi America, Ltd. Semiconductor & IC Div. 2000 Sierra Point Parlaway Briabana, CA. 94005-4835 U.S.A. Tat 445-589-8800

Fex: 415-583-4207

Hitechi Burope GmbH
Bedronic Componente Group
Cartinertal Burope
Darnecher Streße 3
D-85622 Feldkirchen
München
Tet 089-9 94 80-0
Fex: 089-9 29 30 00

Hitachi Burope Ltd.
Bedronic Componenta Div.
Northern Burope Headquartera
Whitborook Fark
Lower Cook hem Road
Heidenhead
Barkshire SL 68YA
Urited Kingdon
Tet 0628-885000
Fex: 0628-778322

Hitachi Asia Pta, Ltd 45 Collyer Quay \$20-00 Hitachi Tower Snappore 0404 Tet 535-2400 Fex 535-4533

Hitachi Asia (Hong Kong) Ltd. Unit 705, North Towar, World Finance Cantra, Harbour City, Carton Road Taim She Taul, Kowloon Hong Kong Tet 27:350218 Fax: 27:306074